AMENDMENTS TO THE SPECIFICATION:

Kindly replace the paragraph beginning on page 15, line 2, with the following amended paragraph:

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A part of or entirety of the insulation gap layer 76 is made of an insulation materials such as Si_3N_4 , $Co-\gamma Fe_2O_3$ (hematite) (maghemite) or SiO_2 that has a lower dielectric constant than Al_2O_3 . The first insulation layer 77 and the second insulation layer 78 are usually made of Al_2O_3 . However, the first insulation layer 77 and the second insulation layer 78 may be made of the same insulation material as that of the insulation gap layer 76.

Kindly replace the paragraph beginning on page 15, line 17, with the following amended paragraph:

1

An important aspect of this embodiment is that a part of or entirety of the insulation gap layer 76 is made of Si₃N₄, Co-γFe₂O₃ (hematite) (maghemite) or SiO₂. Such insulation material has a lower dielectric constant than Al₂O₃ and therefore a dielectric constant of the dielectric material sandwiched between the lower gap layer 71 and the upper gap layer 73 and of the dielectric material sandwiched between the upper gap layer and the lower shield layer 70 under the second lead conductor 82 and the second via hole conductor 83. As a result, the capacitance C_{shield} between the lower and upper shield layers 70 and 74 is reduced to extremely improve the frequency characteristics of the thin-film magnetic head.

Kindly replace the paragraph beginning on page 16, line 25 and ending on page 17, line 4, with the following amended paragraph:

6

If the whole of the insulation gap layer 76 is made of Co- γ Fe₂O₃ (hematite) (maghemite) with a relative dielectric constant of ϵ_r = 3.5, the frequency characteristics of the thin-film magnetic head can be more greatly improved as C_{shield} = 5.1 pF and fc = 240 MHz.

Kindly replace the paragraph beginning on page 22, line 7, with the following amended paragraph:

B

If the whole of the insulation gap layer 76 is made of Co- γ Fe₂O₃ (hematite) (maghemite) with a relative dielectric constant of ϵ_r = 3.5, the frequency characteristics of the thin-film magnetic head can be more greatly improved as C_{shield} = 5.1 pF and fc = 1.04 GHz.